This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-24 (canceled).

Claim 25 (original): A method for manufacturing a surface acoustic wave device using a Shear Horizontal type surface acoustic wave, comprising the steps of:

preparing a quartz substrate;

forming a metal film having a larger mass-load effect than that of aluminum on the quartz substrate; and

patterning the metal film to form at least one interdigital transducer by one of reactive ion etching and a lift-off process such that a metallization ratio "d" and a normalized film thickness h/λ of the at least one interdigital transducer which makes a spurious transversal mode ripple to be about 1.5 dB or less are satisfied, where "d" is the metallization ratio of the interdigital transducer, "λ" is the wavelength of a surface acoustic wave, and "h" is the film thickness of the interdigital transducer.

Claim 26 (original): A method according to Claim 25, wherein the metal film is made from tantalum, and patterning is performed such that the normalized film thickness h/λ is within a range of about $0.6d + 1.50$ to about $0.65d + 1.87$ to form the at least one interdigital transducer.

Claim 27 (original): A method according to Claim 26, wherein patterning is performed such that the normalized film thickness h/λ of the at least one interdigital transducer is within a range of about $0.6d + 1.65$ to about $0.6d + 1.81$.

Claim 28 (original): A method according to Claim 25, wherein the metal film is made from tungsten, and patterning is performed such that the normalized film thickness h/λ is within a range from about $0.6d + 0.85$ to about $0.6d + 1.30$ to form the at least one interdigital transducer.

Claim 29 (original): A method according to Claim 28, wherein patterning is performed such that the normalized film thickness h/λ of the interdigital transducer is within a range from about $0.6d + 1.00$ to about $0.6d + 1.23$.